BUV22

Switch-mode Series NPN Silicon Power Transistor

This device is designed for high speed, high current, high power applications.

Features

• High DC Current Gain:

 $h_{FE} \min = 20 \text{ at } I_C = 10 \text{ A}$

• Low V_{CE(sat)}, V_{CE(sat)}

 $max = 1.0 \text{ V at } I_C = 10 \text{ A}$

• Very Fast Switching Times:

TF max = $0.35 \mu s$ at $I_C = 20 A$

• Pb-Free Package is Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|------------|------------|
| Collector–Emitter Voltage | V _{CEO(SUS)} | 250 | Vdc |
| Collector-Base Voltage | V_{CBO} | 300 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 7 | Vdc |
| Collector–Emitter Voltage (V _{BE} = -1.5 V) | V _{CEX} | 300 | Vdc |
| Collector–Emitter Voltage (R _{BE} = 100 Ω) | V _{CER} | 290 | Vdc |
| Collector-Current - Continuous - Peak (PW ≤ 10 ms) | I _C I _{CM} | 40 50 | Adc Apk |
| Base-Current Continuous | Ι _Β | 8 | Adc |
| Total Device Dissipation @ T _C = 25°C | P _D | 250 | W |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to 200 | °C |

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Max | Unit |
|--------------------------------------|---------------|-----|------|
| Thermal Resistance, Junction-to-Case | θ_{JC} | 0.7 | °C/W |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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40 AMPERES NPN SILICON POWER METAL TRANSISTOR 250 VOLTS - 250 WATTS



TO-204AE (TO-3) CASE 197A

MARKING DIAGRAM



BUV22 = Device Code G = Pb-Free Package A = Assembly Location

Y = Year WW = Work Week MEX = Country of Origin

ORDERING INFORMATION

| Device | Package | Shipping |
|--------|---------------------|------------------|
| BUV22 | TO-204 | 100 Units / Tray |
| BUV22G | TO-204 (Pb-Free) | 100 Units / Tray |

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BUV22

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

| | Characteristic | Symbol | Min | Max | Unit |
|---|--|--|------------|-------------|----------|
| OFF CHARACTERISTICS (Note | e 1) | | | | |
| Collector–Emitter Sustaining Vo | - | V _{CEO(sus)} | 250 | | Vdc |
| Collector Cutoff Current at Rev $(V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V})$ $(V_{CE} = 300 \text{ V}, V_{BE} = -1.5 \text{ V})$ | | ICEX | | 3.0 12.0 | mAdc |
| Collector–Emitter Cutoff Currer (V _{CE} = 200 V) | nt | I _{CEO} | | 3.0 | mAdc |
| Emitter–Base Reverse Voltage (I _E = 50 mA) | | V _{EBO} | 7 | | V |
| Emitter–Cutoff Current (V _{EB} = 5 V) | | I _{EBO} | | 1.0 | mAdc |
| SECOND BREAKDOWN | | <u> </u> | | • | |
| Second Breakdown Collector C (V _{CE} = 20 V, t = 1 s) (V _{CE} = 140 V, t = 1 s) | Current with base forward biased | I _{S/b} | 12 0.15 | | Adc |
| ON CHARACTERISTICS (Note | 1) | | | • | • |
| DC Current Gain (I _C = 10 A, V _{CE} = 4 V) (I _C = 20 A, V _{CE} = 4 V) | | h _{FE} | 20 10 | 60 | |
| Collector–Emitter Saturation Vo ($I_C = 10 \text{ A}, I_B = 1 \text{ A}$) ($I_C = 20 \text{ A}, I_B = 2.5 \text{ A}$) | oltage | V _{CE(sat)} | | 1.0 1.5 | Vdc |
| Base–Emitter Saturation Voltage (I _C = 40 A, I _B = 4 A) | | V _{BE(sat)} | | 1.5 | Vdc |
| DYNAMIC CHARACTERISTICS | 3 | , | | | • |
| Current Gain — Bandwidth Pro (V _{CE} = 15 V, I _C = 2 A, f = 4 M | | f _T | 8.0 | | MHz |
| SWITCHING CHARACTERISTI | CS (Resistive Load) | <u>. </u> | | • | • |
| Turn-on Time | | t _{on} | | 0.8 | μs |
| Storage Time | $(I_C = 20 \text{ A}, I_{B1} = I_{B2} = 2.5 \text{ A},$ $V_{CC} = 100 \text{ V}, R_C = 5 \Omega)$ | t _s | | 2.0 | 1 |
| Fall Time | 100 100 1,110 0 22) | t _f | | 0.35 | <u> </u> |
| - | | | | | |

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2\%$.

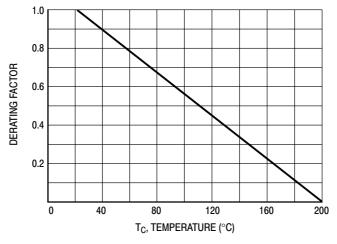


Figure 1. Power Derating

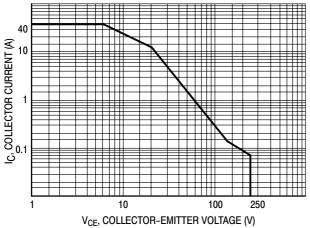


Figure 2. Active Region Safe Operating Area

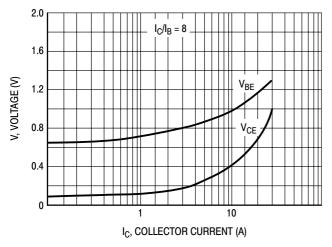


Figure 3. "On" Voltages

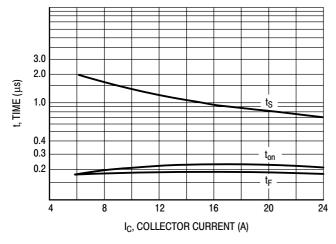


Figure 5. Resistive Switching Performance

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can handled to values less than the limitations imposed by second breakdown.

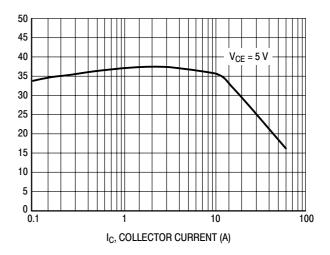
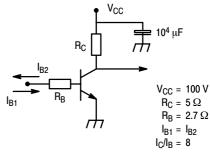


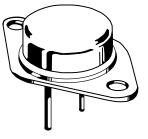
Figure 4. DC Current Gain



R_C - R_B: Non inductive resistances

Figure 6. Switching Times Test Circuit

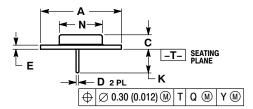


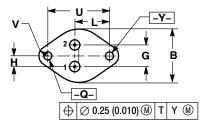


TO-204 (TO-3) **CASE 197A-05 ISSUE K**

DATE 21 FEB 2000

SCALE 1:1





STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

STYLE 2: PIN 1. EMITTER 2. BASE

CASE: COLLECTOR

STYLE 3: PIN 1. GATE 2. SOURCE CASE: DRAIN

STYLE 4: PIN 1. ANODE = 1 2. ANODE = 2 CASE: CATHODES

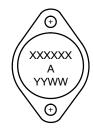
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

| | INC | CHES MILLIMETERS | | |
|-----|-----------|------------------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.530 | REF | 38.86 REF | |
| В | 0.990 | 1.050 | 25.15 | 26.67 |
| C | 0.250 | 0.335 | 6.35 | 8.51 |
| D | 0.057 | 0.063 | 1.45 | 1.60 |
| Е | 0.060 | 0.070 | 1.53 | 1.77 |
| G | 0.430 | BSC | 10.92 BSC | |
| Н | 0.215 | BSC | 5.46 BSC | |
| K | 0.440 | 0.480 | 11.18 | 12.19 |
| L | 0.665 BSC | | 16.89 BSC | |
| N | 0.760 | 0.830 | 19.31 | 21.08 |
| Q | 0.151 | 0.165 | 3.84 | 4.19 |
| כ | 1.187 | 1.187 BSC | | BSC |
| ٧ | 0.131 | 0.188 | 3.33 | 4.77 |

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Locationa Α

YY = Year WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking.

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| DESCRIPTION: | TO-204 (TO-3) | | PAGE 1 OF 2 |



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PAGE 2 OF 2

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